

## Excellent Integrated System Limited

Stocking Distributor

Click to view price, real time Inventory, Delivery & Lifecycle Information:

[Diodes Incorporated](#)  
[DRDNB21D-7](#)

For any questions, you can email us directly:

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**DRDNB21D**

**COMPLEX ARRAY FOR DUAL RELAY DRIVER**

**Features and Benefits**

- Epitaxial Planar Die Construction
- Two Pre-Biased Transistors and Two Switching Diodes, Internally Connected in One Package
- Ideally Suited for Automated Assembly Processes
- **Lead Free By Design/RoHS Compliant (Note 1)**
- **"Green" Device (Note 2)**
- **Qualified to AEC-Q101 standards for High Reliability**

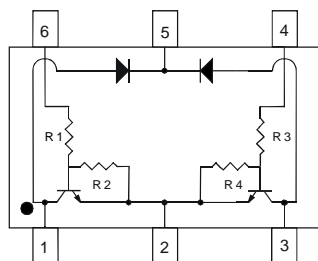
R1 = R3 = 2.2kΩ (nominal)  
 R2 = R4 = 47kΩ (nominal)

**Mechanical Data**

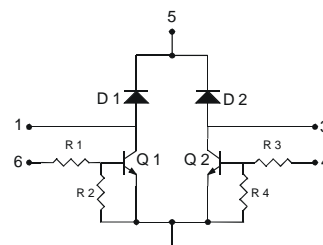
- Case: SOT-363
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish - Matte Tin annealed over Alloy 42 leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.0062 grams (approximate)



Top View



Top View



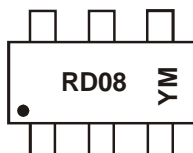
Device Circuit

**Ordering Information (Note 3)**

| Device     | Packaging | Shipping         |
|------------|-----------|------------------|
| DRDNB21D-7 | SOT-363   | 3000/Tape & Reel |

- Notes:
1. No purposefully added lead.
  2. Diodes Inc.'s "Green" Policy can be found on our website at <http://www.diodes.com>
  3. For packaging details, visit our website at <http://www.diodes.com>.

**Marking Information**



RD08 = Product Type Marking Code  
 YM = Date Code Marking  
 Y = Year (e.g. T = 2006)  
 M = Month (e.g. 1 = January)

Date Code Key

| Year  | 2005 | 2006 | 2007 | 2008 | 2009 | 2010 | 2011 | 2012 | 2013 | 2014 | 2015 | 2016 |
|-------|------|------|------|------|------|------|------|------|------|------|------|------|
| Code  | S    | T    | U    | V    | W    | X    | Y    | Z    | A    | B    | C    | D    |
| Month | Jan  | Feb  | Mar  | Apr  | May  | Jun  | Jul  | Aug  | Sep  | Oct  | Nov  | Dec  |
| Code  | 1    | 2    | 3    | 4    | 5    | 6    | 7    | 8    | 9    | O    | N    | D    |

**Maximum Ratings, Total Device** @ $T_A = 25^\circ\text{C}$  unless otherwise specified

| Characteristic                                       | Symbol          | Value       | Unit               |
|--|-----------------|-------------|--------------------|
| Power Dissipation (Note 4)                           | $P_D$           | 200         | mW                 |
| Thermal Resistance, Junction to Ambient Air (Note 4) | $R_{\theta JA}$ | 625         | $^\circ\text{C/W}$ |
| Operating and Storage Junction Temperature Range     | $T_J, T_{STG}$  | -55 to +150 | $^\circ\text{C}$   |

**Maximum Ratings, Pre-Biased NPN Transistor** @ $T_A = 25^\circ\text{C}$  unless otherwise specified

| Characteristic            | Symbol   | Value     | Unit |
|---------------------------|----------|-----------|------|
| Collector-Emitter Voltage | $V_{CC}$ | 50        | V    |
| Base-Emitter Voltage      | $V_{in}$ | -5 to +12 | V    |
| Output Current            | $I_O$    | 100       | mA   |
| Peak Collector Current    | $I_{CM}$ | 100       | mA   |

**Maximum Ratings, Switching Diode** @ $T_A = 25^\circ\text{C}$  unless otherwise specified

| Characteristic   | Symbol       | Value | Unit |
|--|--------------|-------|------|
| Non-Repetitive Peak Reverse Voltage                              | $V_{RM}$     | 100   | V    |
| Peak Repetitive Reverse Voltage                                  | $V_{RRM}$    | 75    | V    |
| Working Peak Reverse Voltage                                     | $V_{RWM}$    |       |      |
| DC Blocking Voltage  | $V_R$        |       |      |
| RMS Reverse Voltage  | $V_{R(RMS)}$ | 53    | V    |
| Forward Continuous Current (Note 4)                              | $I_{FM}$     | 500   | mA   |
| Average Rectified Output Current (Note 4)                        | $I_O$        | 250   | mA   |
| Non-Repetitive Peak Forward Surge Current @ $t = 1.0\mu\text{s}$ | $I_{FSM}$    | 4.0   | A    |
| @ $t = 1.0\text{s}$  |              | 1.0   |      |

**Electrical Characteristics, Pre-Biased NPN Transistor** @ $T_A = 25^\circ\text{C}$  unless otherwise specified

| Characteristic             | Symbol         | Min | Typ | Max | Unit          | Test Condition   |
|----------------------------|----------------|-----|-----|-----|---------------|--|
| Input Voltage              | $V_{I(off)}$   | 0.5 | —   | —   | V             | $V_{CC} = 5\text{V}, I_O = 100\mu\text{A}$                 |
|                            | $V_{I(on)}$    | —   | —   | 1.1 | V             | $V_O = 0.3\text{V}, I_O = 5\text{mA}$                      |
| Output Voltage             | $V_{O(on)}$    | —   | —   | 0.3 | V             | $I_O/I_I = 50\text{mA}/0.25\text{mA}$                      |
| Input Current              | $I_I$          | —   | —   | 3.6 | mA            | $V_I = 5\text{V}$  |
| Output Current             | $I_{O(off)}$   | —   | —   | 0.5 | $\mu\text{A}$ | $V_{CC} = 50\text{V}, V_I = 0\text{V}$                     |
| DC Current Gain            | $G_I$          | 80  | —   | —   | —             | $V_O = 5\text{V}, I_O = 10\text{mA}$                       |
| Input Resistor Tolerance   | $\Delta R1$    | -30 | —   | +30 | %             | -  |
| Resistance Ratio Tolerance | $\Delta R2/R1$ | -20 | —   | +20 | %             | -  |
| Gain-Bandwidth Product*    | $f_T$          | —   | 250 | —   | MHz           | $V_{CE} = 10\text{V}, I_E = 5\text{mA}, f = 100\text{MHz}$ |

\* Transistor - For Reference Only

**Electrical Characteristics, Switching Diode** @ $T_A = 25^\circ\text{C}$  unless otherwise specified

| Characteristic                     | Symbol      | Min  | Max   | Unit          | Test Condition  |
|------------------------------------|-------------|------|-------|---------------|---|
| Reverse Breakdown Voltage (Note 5) | $V_{(BR)R}$ | 75   | —     | V             | $I_R = 10\mu\text{A}$   |
| Forward Voltage                    | $V_F$       | 0.62 | 0.72  | V             | $I_F = 5.0\text{mA}$  |
|                                    |             | —    | 0.855 |               | $I_F = 10\text{mA}$   |
|                                    |             | —    | 1.0   |               | $I_F = 100\text{mA}$  |
|                                    |             | —    | 1.25  |               | $I_F = 150\text{mA}$  |
| Reverse Current (Note 5)           | $I_R$       | —    | 2.5   | $\mu\text{A}$ | $V_R = 75\text{V}$  |
|                                    |             | —    | 50    | $\mu\text{A}$ | $V_R = 75\text{V}, T_J = 150^\circ\text{C}$                         |
|                                    |             | —    | 30    | $\mu\text{A}$ | $V_R = 25\text{V}, T_J = 150^\circ\text{C}$                         |
|                                    |             | —    | 25    | nA            | $V_R = 20\text{V}$  |
| Total Capacitance                  | $C_T$       | —    | 4.0   | pF            | $V_R = 0, f = 1.0\text{MHz}$  |
| Reverse Recovery Time              | $t_{rr}$    | —    | 4.0   | ns            | $I_F = I_R = 10\text{mA}, I_{rr} = 0.1 \times I_R, R_L = 100\Omega$ |

 Notes: 4. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at <http://www.diodes.com>  
 5. Short duration pulse test used to minimize self-heating effect.

**Device Characteristics**

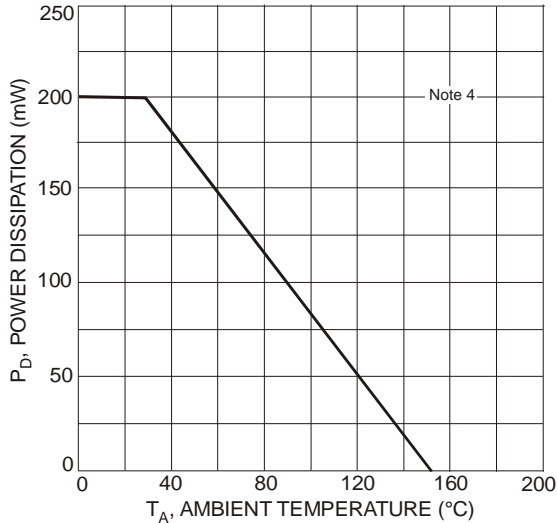


Fig. 1 Power Derating Curve (Total Device)

**Pre-Biased NPN Transistor Elements**

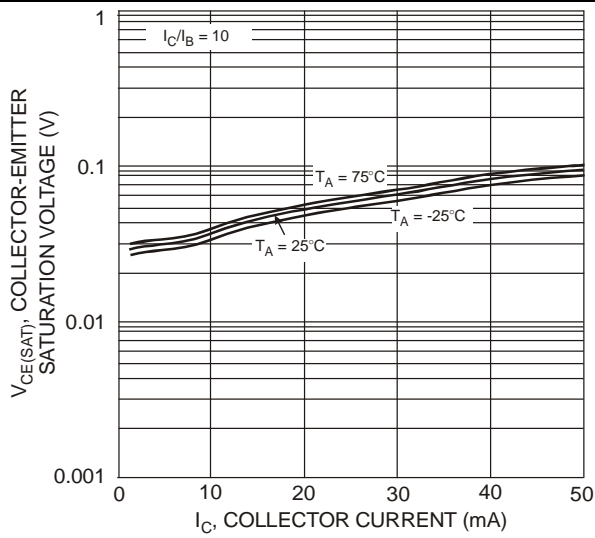


Fig. 2 Typical  $V_{CE(SAT)}$  vs.  $I_C$

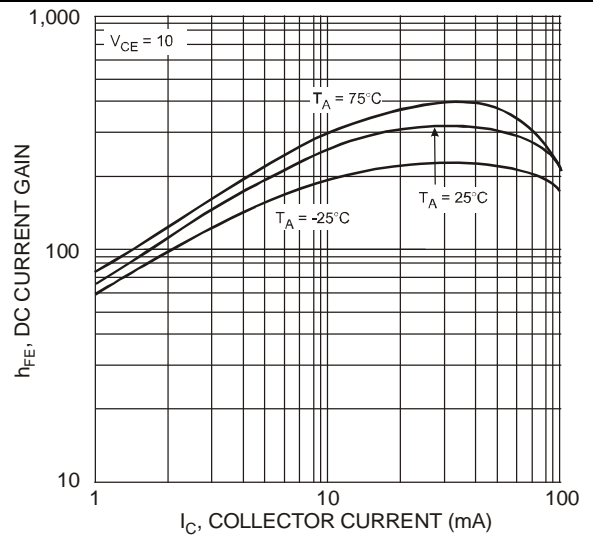


Fig. 3 Typical DC Current Gain

**Pre-Biased NPN Transistor Elements - continued**

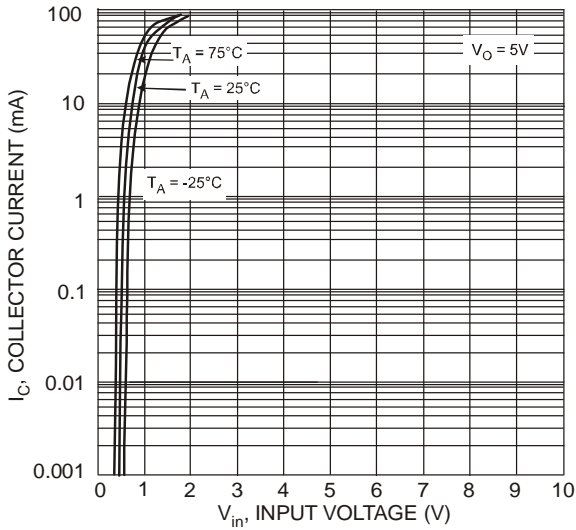


Fig. 4 Typical Collector Current vs. Input Voltage

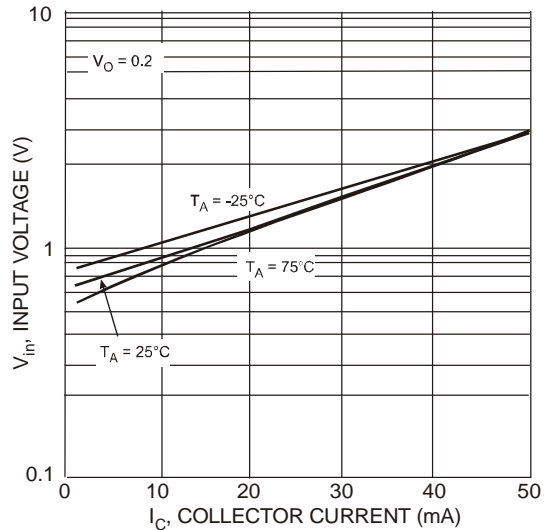


Fig. 5 Typical Input Voltage vs. Collector Current

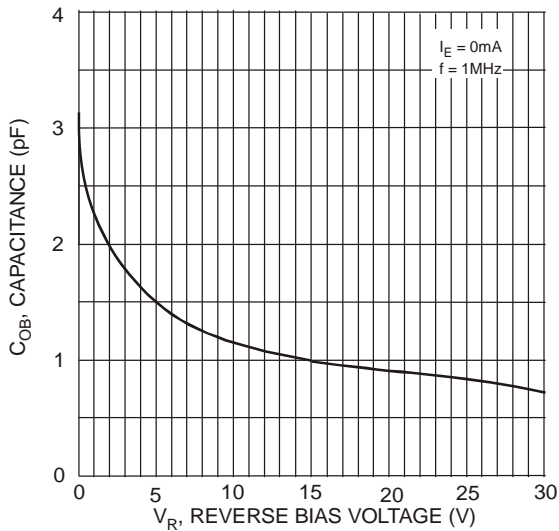


Fig. 6 Typical Output Capacitance

**Switching Diode Elements**

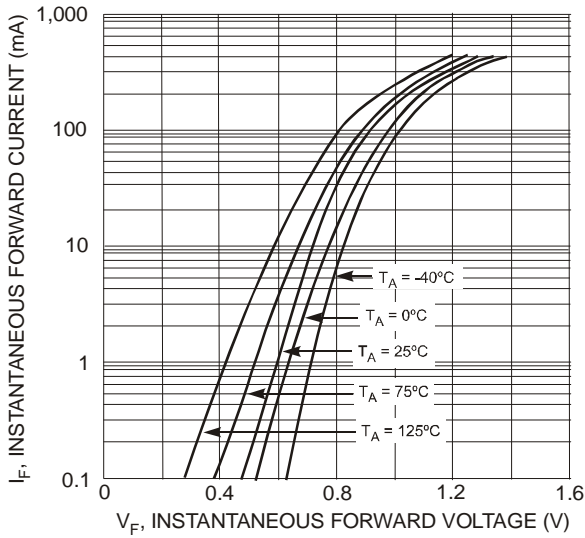


Fig. 7 Typical Forward Characteristics

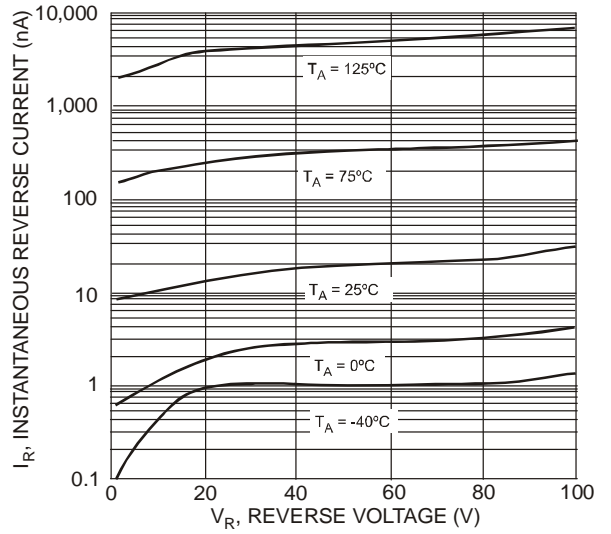


Fig. 8 Typical Reverse Characteristics

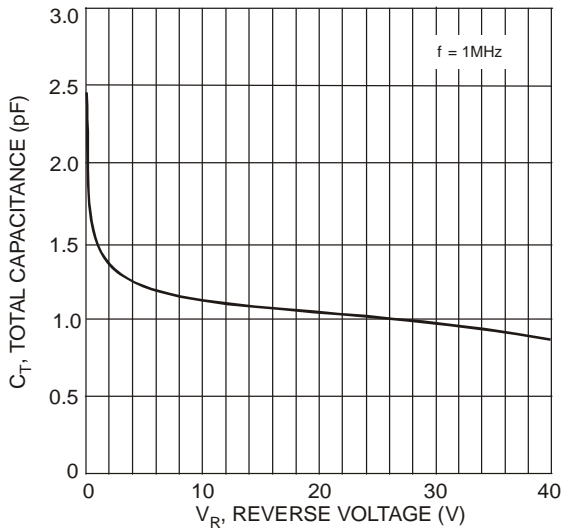
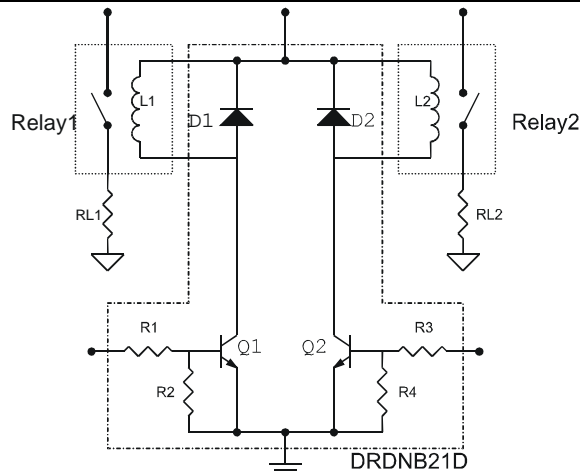


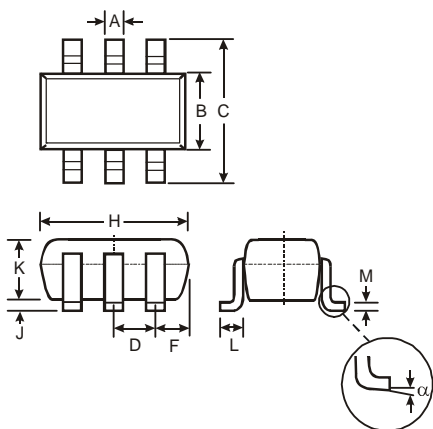
Fig. 9 Typical Capacitance vs. Reverse Voltage

**Typical Application Circuit**



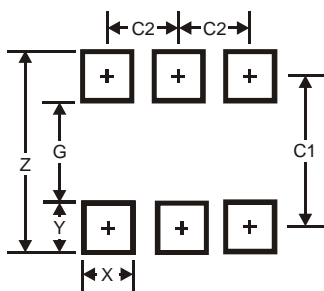
Typical Application Circuit DRDNB21D with two independent relays.

**Package Outline Dimensions**



| SOT-363              |          |      |
|----------------------|----------|------|
| Dim                  | Min      | Max  |
| A                    | 0.10     | 0.30 |
| B                    | 1.15     | 1.35 |
| C                    | 2.00     | 2.20 |
| D                    | 0.65 Typ |      |
| F                    | 0.40     | 0.45 |
| H                    | 1.80     | 2.20 |
| J                    | 0        | 0.10 |
| K                    | 0.90     | 1.00 |
| L                    | 0.25     | 0.40 |
| M                    | 0.10     | 0.22 |
| α                    | 0°       | 8°   |
| All Dimensions in mm |          |      |

**Suggested Pad Layout**



| Dimensions | Value (in mm) |
|------------|---------------|
| Z          | 2.5           |
| G          | 1.3           |
| X          | 0.42          |
| Y          | 0.6           |
| C1         | 1.9           |
| C2         | 0.65          |

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